

FC8V33030L **Dual N-channel MOSFET** 

For switching For DC-DC Converter

- Features
- · Low drain-source On-state Resistance : RDS(on) typ = 22 m $\Omega$  (VGS = 4.5 V)
- High-speed switching : Qg = 3.8 nC
- · Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: 6A

Basic Part Number : Dual Nch MOS 33V (Individual)

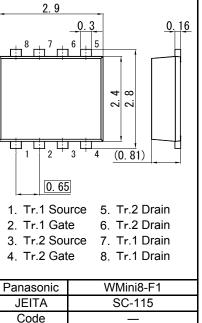
#### Packaging

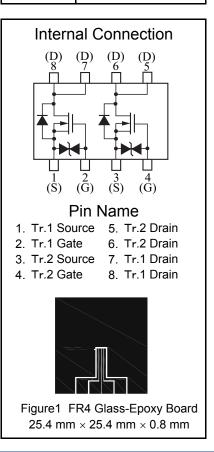
Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C Tr.1, Tr.2 Parameter Symbol Rating Unit Drain-source Voltage VDS 33 V Gate-source Voltage VGS ±20 V 6.5 Drain Current (Steady State) ID 8 Drain Current (t = 10 s) IDp 26 Drain Current (Pulsed) А Source Current (Pulsed) ISp 6.5 (Body Diode) \*1,\*2 (BD) Total Power Dissipation (Steady State) 1 PD W 1.5 Total Power Dissipation (t = 10 s) Tch 150 °C Channel Temperature Operating Ambient Temperature Topr -40 to + 85 °C Storage Temperature Range Tstg -55 to +150 °C

Note) \*1 Device mounted on a glass-epoxy board (See Figure 1)

\*2 Pulse test: Ensure that the channel temperature does not exceed 150°C.





Unit: mm

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# **Panasonic**

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#### ■ Electrical Characteristics Ta = 25°C ± 3°C Tr.1, Tr.2

### Static Characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	33			V
Zero Gate Voltage Drain Current	IDSS	VDS = 33 V, VGS = 0 V			10	μA
Gate-source Leakage Current	IGSS	VGS = ±16 V, VDS = 0 V			±10	μA
Gate-source Threshold Voltage	Vth	ID = 0.48 mA, VDS = 10 V	1		2.5	V
Drain-source On-state Resistance <sup>*1</sup>	RDS(on)1	ID = 3.3 A, VGS = 10 V		15	20	mΩ
	RDS(on)2	ID = 3.3 A, VGS = 4.5 V		22	35	

#### **Dynamic Characteristics**

Input Capacitance	Ciss	VDS = 10 V, VGS = 0 V	360	
Output Capacitance	Coss	f = 1 MHz	70	pF
Reverse Transfer Capacitance	Crss		50	
Turn-on Delay Time <sup>*2</sup>	td(on)	VDD = 15 V, VGS = 0 to 10 V	8	
Rise Time <sup>*2</sup>	tr	ID = 3.3 A	3	ns
Turn-off Delay Time *2	td(off)	VDD = 15 V, VGS = 10 to 0 V	24	115
Fall Time <sup>*2</sup>	tf	ID = 3.3 A	9	
Total Gate Charge	Qg	VDD = 15 V, VGS = 0 to 4.5 V,	3.8	
Gate-source Charge	Qgs	ID = 6.5 A	1.4	nC
Gate-drain Charge	Qgd		1.6	

#### Body Diode Characteristic

Diode Forward Voltage *1	VSD	IS = 3.3 A, VGS = 0 V	0.8	1.2	V			
Nete) 4. Measuring methods are based on IADANEOE INDUCTRIAL OTANDADD, U.O. 7000 Measuring methods for the sister								

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

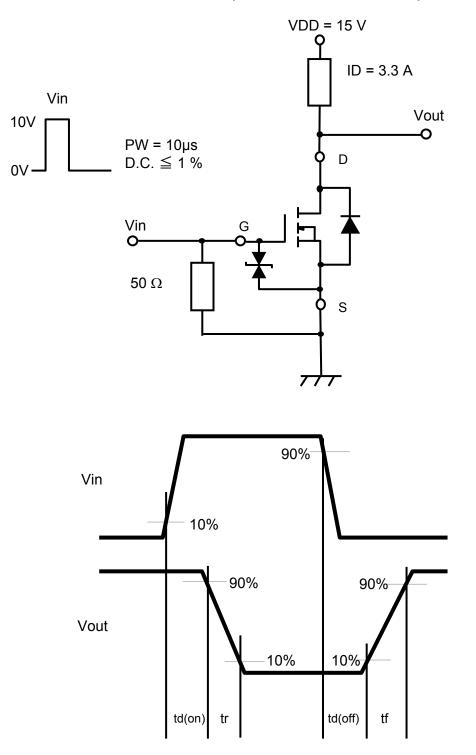
2. \*1 Pulse test: Ensure that the channel temperature does not exceed 150°C.

\*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

Doc No. TT4-EA-13171 Revision. 2

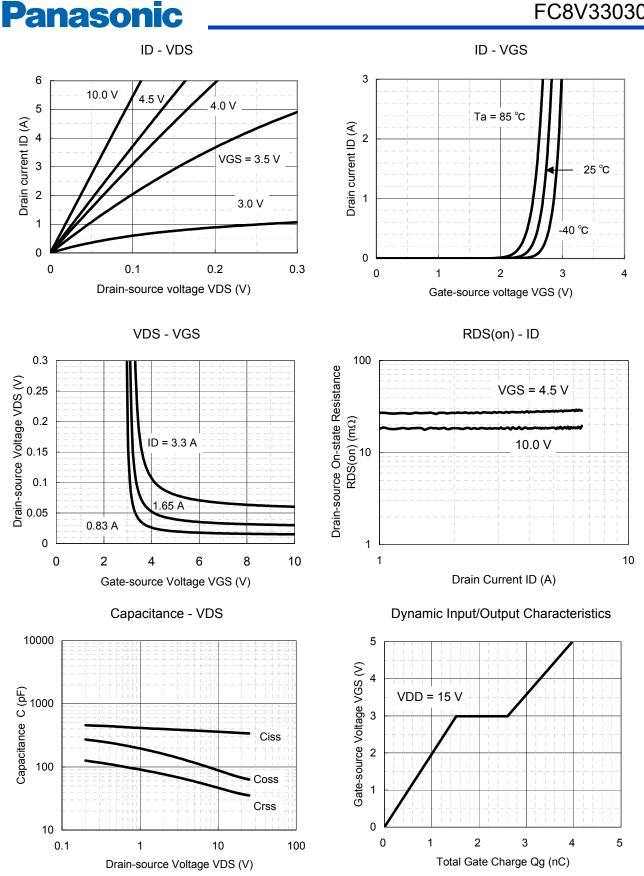


\*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time



Established : 2011-04-20 Revised : 2013-07-31

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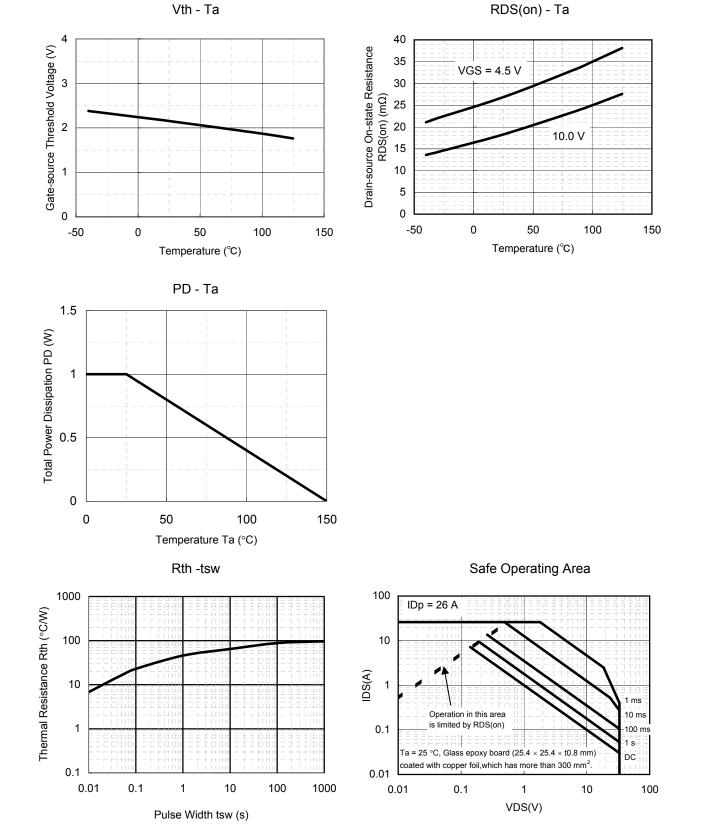


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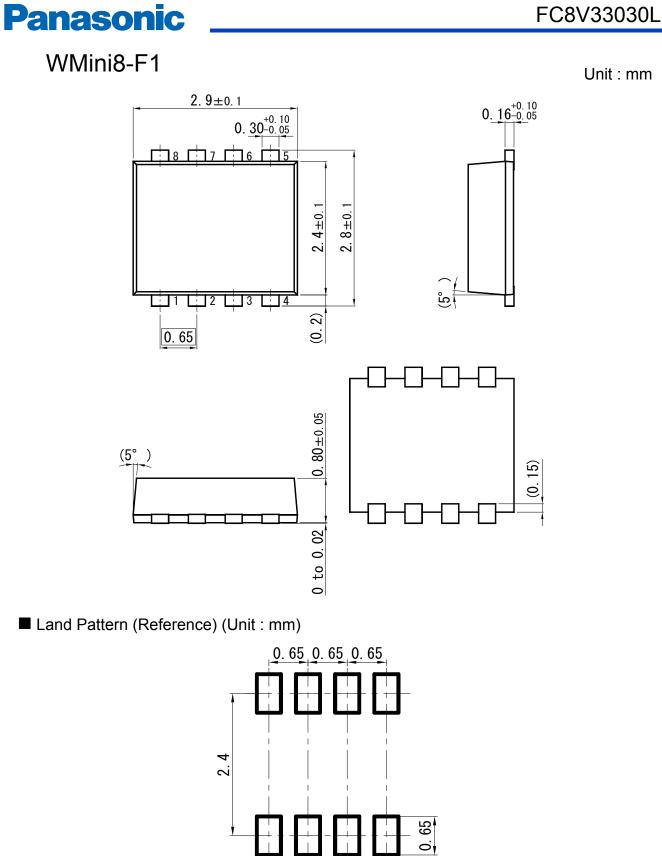
**Panasonic** 



MOS FET

FC8V33030L

Established : 2011-04-20 Revised : 2013-07-31



0.4

Unit : mm

MOS FET

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